

501.36931X00
Expedited Procedure Requested
Amendment Under 37 CFR 1.116
Group 2813

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): IWASAKI, et al.
Serial No.: 09/255,856
Filed: February 23, 1999
For: SEMICONDUCTOR DEVICE WITH LAYERED INTERCONNECT
STRUCTURE
Group: 2813
Examiner: S. Smoot

AMENDMENT AFTER FINAL REJECTION

Assistant Commissioner for Patents
Box AF
Washington, D.C. 20231

May 14, 2001

Sir:

In response to the Office Action mailed December 11,
2000, please amend the above-identified application as
follows:

IN THE CLAIMS

Please cancel claims 8, 21 and 26 without prejudice or
disclaimer, and amend the claims remaining in the application
as follows:

1. (Amended) A semiconductor device with a multilayered
structure comprising a copper film interconnect formed on one
primary surface of a semiconductor substrate, and a
neighboring film formed in contact with said copper film
interconnect, wherein said neighboring film is formed of a